

CD74HC4049, CD74HC4050

High-Speed CMOS Logic Hex Buffers, Inverting and Non-Inverting

Features

- Typical Propagation Delay: 6ns at $V_{CC} = 5V$, $C_L = 15pF$, $T_A = 25^\circ C$
- High-to-Low Voltage Level Converter for up to $V_I = 16V$
- Fanout (Over Temperature Range)
 - Standard Outputs 10 LSTTL Loads
 - Bus Driver Outputs 15 LSTTL Loads
- Wide Operating Temperature Range . . . $-55^\circ C$ to $125^\circ C$
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
 - 2V to 6V Operation
 - High Noise Immunity: $N_{IL} = 30\%$, $N_{IH} = 30\%$ of V_{CC} at $V_{CC} = 5V$

Description

The CD74HC4049 and CD74HC4050 are fabricated with high-speed silicon gate technology. They have a modified input protection structure that enables these parts to be used as logic level translators which convert high-level logic to a low-level logic while operating off the low-level logic supply. For example, 15-V input pulse levels can be down-converted to 0-V to 5-V logic levels. The modified input protection structure protects the input from negative electrostatic discharge. These parts also can be used as simple buffers or inverters without level translation. The CD74HC4049 and CD74HC4050 are enhanced versions of equivalent CMOS types.

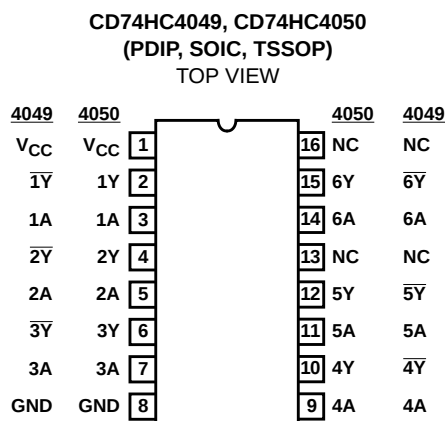
Ordering Information

PART NUMBER	TEMP. RANGE ($^\circ C$)	PACKAGE	PKG. NO.
CD74HC4049E	-55 to 125	16 Ld PDIP	E16.3
CD74HC4050E	-55 to 125	16 Ld PDIP	E16.3
CD74HC4049M	-55 to 125	16 Ld SOIC	M16.15
CD74HC4050M	-55 to 125	16 Ld SOIC	M16.15
CD74HC4050PW	-55 to 125	16 Ld TSSOP	

NOTES:

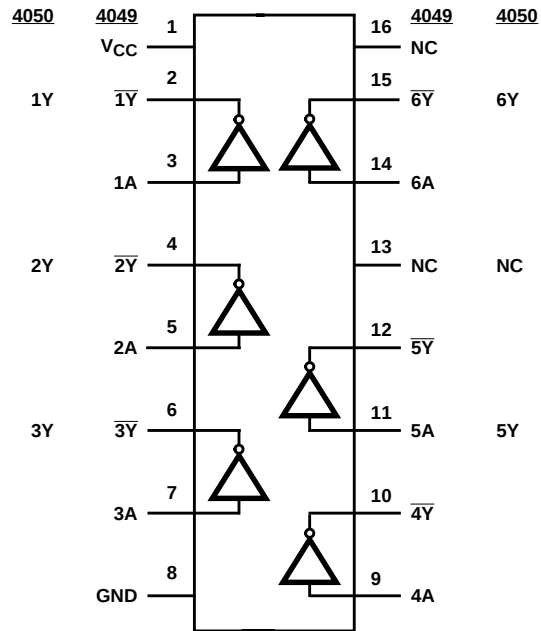
1. When ordering, use the entire part number. Add the suffix 96 to the M suffix or the R suffix to the PW package to obtain the variant in the tape and reel.
2. Wafer and die is available which meets all electrical specifications. Please contact your local sales office or customer service for ordering information.

Pinout



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Functional Diagram

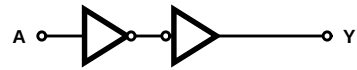


Logic Diagrams

HC4049



HC4050



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Absolute Maximum Ratings

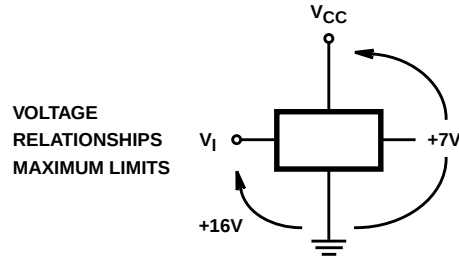
DC Supply Voltage, V_{CC} -0.5V to 7V
 DC Input Diode Current, I_{IK}
 For $V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$ $\pm 20mA$
 DC Output Diode Current, I_{OK}
 For $V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$ $\pm 20mA$
 DC Output Source or Sink Current per Output Pin, I_O
 For $V_O > -0.5V$ or $V_O < V_{CC} + 0.5V$ $\pm 25mA$
 DC V_{CC} or Ground Current, I_{CC} or I_{GND} $\pm 50mA$

Operating Conditions

Temperature Range (T_A) -55°C to 125°C
 Supply Voltage Range, V_{CC}
 HC Types 2V to 6V
 HCT Types 4.5V to 5.5V
 DC Input or Output Voltage, V_I , V_O 0V to V_{CC}
 Input Rise and Fall Time
 2V 1000ns (Max)
 4.5V 500ns (Max)
 6V 400ns (Max)

Thermal Information

Thermal Resistance (Typical, Note 3) θ_{JA} (°C/W)
 PDIP Package 78
 SOIC Package 113
 TSSOP Package 149
 Maximum Junction Temperature (Hermetic Package or Die) ... 175°C
 Maximum Junction Temperature (Plastic Package) 150°C
 Maximum Storage Temperature Range -65°C to 150°C
 Maximum Lead Temperature (Soldering 10s) 300°C
 (SOIC - Lead Tips Only)



CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

- θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

DC Electrical Specifications

PARAMETER	SYMBOL	TEST CONDITIONS		V _{CC} (V)	25°C			−40°C TO 85°C		−55°C TO 125°C		UNITS
		V _I (V)	I _O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES												
High Level Input Voltage	V _{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V
				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input Voltage	V _{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V
				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output Voltage CMOS Loads	V _{OH}	V _{IH} or V _{IL}	−0.02	2	1.9	-	-	1.9	-	1.9	-	V
			−0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
			−0.02	6	5.9	-	-	5.9	-	5.9	-	V
−4			4.5	3.98	-	-	3.84	-	3.7	-	V	
−5.2			6	5.48	-	-	5.34	-	5.2	-	V	
Low Level Output Voltage CMOS Loads			V _{OL}	V _{IH} or V _{IL}	0.02	2	-	-	0.1	-	0.1	-
	0.02	4.5			-	-	0.1	-	0.1	-	0.1	V
	0.02	6			-	-	0.1	-	0.1	-	0.1	V
	4	4.5			-	-	0.26	-	0.33	-	0.4	V
	5.2	6			-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I _I	V _{CC} or GND	-	6	-	-	±0.1	-	±1	-	±1	μA
		15	-	6	-	-	±0.5	-	±5	-	±5	
Quiescent Device Current	I _{CC}	V _{CC} or GND	0	6	-	-	2	-	20	-	40	μA

NOTE: For dual-supply systems theoretical worst case ($V_I = 2.4V$, $V_{CC} = 5.5V$) specification is 1.8mA.

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Switching Specifications Input $t_r, t_f = 6\text{ns}$

PARAMETER	SYMBOL	TEST CONDITIONS	V _{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES											
Propagation Delay, nA to nY HC4049 nA to nY HC4050	t _{PLH} , t _{PHL}	C _L = 50pF	2	-	-	85	-	105	-	130	ns
			4.5	-	-	17	-	21	-	26	ns
			6	-	-	14	-	18	-	22	ns
		C _L = 15pF	5	-	6	-	-	-	-	-	ns
Transition Times (Figure 1)	t _{TLH} , t _{THL}	C _L = 50pF	2	-	-	75	-	95	-	110	ns
			4.5	-	-	15	-	19	-	22	ns
			6	-	-	13	-	16	-	19	ns
Input Capacitance	C _I	-	-	-	-	10	-	10	-	10	pF
Power Dissipation Capacitance (Notes 4, 5)	C _{PD}	-	5	-	35	-	-	-	-	-	pF

NOTES:

- C_{PD} is used to determine the dynamic power consumption, per gate.
- $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where f_i = Input Frequency, C_L = Output Load Capacitance, V_{CC} = Supply Voltage.

Test Circuit and Waveform

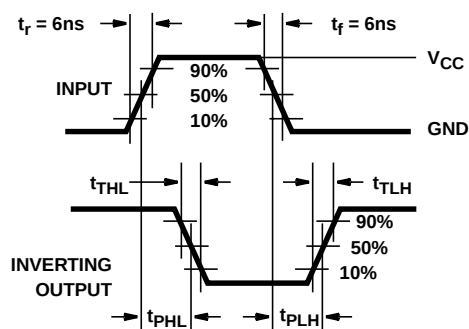


FIGURE 1. HC AND HCU TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

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